

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	826	@ad<="20040329" and (257/328). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:24
S2	219	@ad<="20040329" and (438/212). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:48
S3	635	@ad<="20040329" and (438/268). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:49
S4	1908	@ad<="20040329" and (257/355-356).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:50
S5	463	@ad<="20040329" and (257/357). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:51
S6	58	'NEC' and 'ando takeshi'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:51
S7	1954	@ad<="20040329" and (257/369). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 06:53
S8	2215	@ad<="20040329" and 'CMOS' same 'protection' same 'circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:37
S9	1296	@ad<="20040329" and 'CMOS' with 'protection' with 'circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:02
S10	777	@ad<="20040329" and 'CMOS' with 'protection circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:02

S11	3	@ad<="20040329" and 'CMOS' with 'protection circuit' and 'output electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:04
S12	40	@ad<="20040329" and 'CMOS' with 'protection' and 'surge' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 08:26
S13	235	@ad<="20040329" and 'CMOS' and 'protection' and 'surge' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:05
S14	1150	@ad<="20040329" and 'CMOS' and 'ESD' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:05
S15	422	@ad<="20040329" and 'CMOS' same 'ESD' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 09:43
S16	283	@ad<="20040329" and 'CMOS' with 'ESD' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:06
S17	1833	@ad<="20040329" and (361/56). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:49
S18	1	"6385028".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:24
S19	1	"6249410".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:25
S20	1	"6064249".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:26
S21	1400	@ad<="20040329" and (361/111). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:41
S22	1	"6266222".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:28
S23	1	"6130811".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:28
S24	1	"6034397".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:29
S25	1	"6080612".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:33

S26	1	"5963409".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:33
S27	1	"5086365".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:34
S28	1	"5910874".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:38
S29	1	"5729419".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S30	1	"5644459".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S31	1	"5086365".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S32	1	"5644459".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S33	1	"5499152".PN.	USPAT; USOCR	OR	ON	2005/06/06 07:39
S34	8	@ad<="20040329" and 'Electrostatic damage protection circuit'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:44
S36	1004	@ad<="20040329" and 'ESD protection circuit' and 'CMOS'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:44
S37	830	@ad<="20040329" and 'ESD protection circuit' and 'CMOS' and 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:44
S38	1	@ad<="20040329" and 'ESD protection circuit' and 'CMOS' and 'output electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 07:45
S39	86	@ad<="20040329" and 'CMOS' and 'protection transistor' and 'output transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:48
S40	1	"6066879".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:35
S41	1	"5918127".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:36
S42	1	"6080612".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:38
S43	1	"5610790".PN.	USPAT; USOCR	OR	ON	2005/06/06 08:38
S44	1	"5986867".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:00

S45	1	"5499152".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:00
S46	1	"6388315".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:12
S47	1	"6281554".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:12
S48	1	"6066879".PN.	USPAT; USOCR	OR	ON	2005/06/06 09:38
S49	1	@ad<="20040329" and 'CMOS' and 'protection' and 'outout' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 09:44
S51	7	@ad<="20040329" and 'CMOS' and 'protection MOS' and 'output MOS' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 09:45
S52	139	@ad<="20040329" and 'CMOS' and 'protection' with 'MOS' and 'output' with 'MOS' and 'output pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:20
S53	420	@ad<="20040329" and 'CMOS' same 'output' same 'ESD' same 'protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:26
S54	356	@ad<="20040329" and 'CMOS' same 'output' same 'ESD protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:28
S55	86	@ad<="20040329" and 'CMOS' same 'output pad' same 'ESD protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:28
S56	0	@ad<="20040329" and 'CMOS' same 'output electrode' same 'ESD protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:29
S57	2	@ad<="20040329" and 'CMOS' and 'output electrode' and 'ESD protection'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:29
S58	5	@ad<="20040329" and 'CMOS' same 'protection' same 'circuit' and 'dummy transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:40

S59	9	'Ichikawa Kenji' and 'oki'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:03
S60	2	@ad<="20040329" and 'CMOS' and 'improved electrostatic breakdown resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:44
S61	23	@ad<="20040329" and 'CMOS' and 'electrostatic breakdown resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:44
S62	76	@ad<="20040329" and 'ESD' and 'protection transistor' and 'output transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 10:48
S63	230	Ichikawa-Kenji.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:05
S64	3	Ichikawa-Kenji.in. and 'ESD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:04
S65	13	Ichikawa-Kenji.in. and 'semiconductor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:06
S66	0	'surge current' same 'ON current' same 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:07
S67	0	'surge current' and 'ON current' same 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:07
S68	0	'surge current' and 'ON current' and 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:07
S69	22	'surge current' same 'protection transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:13

S70	1	"6080612".PN.	USPAT; USOCR	OR	ON	2005/06/06 11:11
S71	1	'protection transistor' and 'low' with ('electrostatic discharge' or 'ESD') with 'resistance' and 'electrode pad'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:15
S72	51	'protection transistor' and 'low' with ('electrostatic discharge' or 'ESD') with 'resistance'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/06 11:15
S73	411	@ad<="20040329" and 'output' with ('electrode' or 'pad') and 'MOS' with 'protection' and 'MOS' with 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 10:15
S74	21	@ad<="20040329" and 'output' with ('electrode' or 'pad') and 'MOS' near 'protection' and 'MOS' near 'output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 08:14
S75	1	"6326666".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:37
S76	1	"6281554".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:38
S77	1	"6278160".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:39
S78	1	"6207996".PN.	USPAT; USOCR	OR	ON	2005/06/07 08:39
S79	70	@ad<="20040329" and ('input/output' or 'I/O') and 'protection transistor' and 'output transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 09:48
S80	1	@ad<="20040329" and ('input/output' or 'I/O') and 'MOS protection' and 'MOS output'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 09:22
S81	10	@ad<="20040329" and 'protection transistor' same 'gate' same 'connect' same 'substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 09:28
S82	1	"6232220".PN.	USPAT; USOCR	OR	ON	2005/06/07 09:32
S83	8	@ad<="20040329" and ('input/output' or 'I/O') and 'protection transistor' and 'positive surge'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 09:48

S84	2	"20040195625"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 10:00
S85	107	@ad<="20040329" and 'CMOS' same 'protection' same 'SOI'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:03
S86	84	@ad<="20040329" and 'ESD protection' same 'SOI' same 'bulk'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:03
S87	76	@ad<="20040329" and 'ESD protection' same 'SOI' with 'bulk'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:15
S88	40	@ad<="20040329" and 'ESD protection' with 'SOI' with 'bulk'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:03
S89	227	@ad<="20040329" and 'SOI substrate' with 'bulk substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:16
S90	115	@ad<="20040329" and 'CMOS' and 'SOI substrate' with 'bulk substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:16
S91	24	@ad<="20040329" and 'CMOS' same 'SOI substrate' with 'bulk substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:18
S92	7	@ad<="20040329" and 'CMOS' and 'SOI substrate' with 'bulk substrate' and 'ESD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:18
S93	44	@ad<="20040329" and (361/56). ccls. and 'SOI' and 'ESD'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:50
S94	114	@ad<="20040329" and 'SOI' and 'ESD' and 'CMOS' and 'clamp'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:54

S95	772	@ad<="20040329" and 'ESD' and 'CMOS' and 'clamp'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 11:54
S96	1	"6204537".PN.	USPAT; USOCR	OR	ON	2005/06/07 12:02
S97	1	"6091592".PN.	USPAT; USOCR	OR	ON	2005/06/07 12:02